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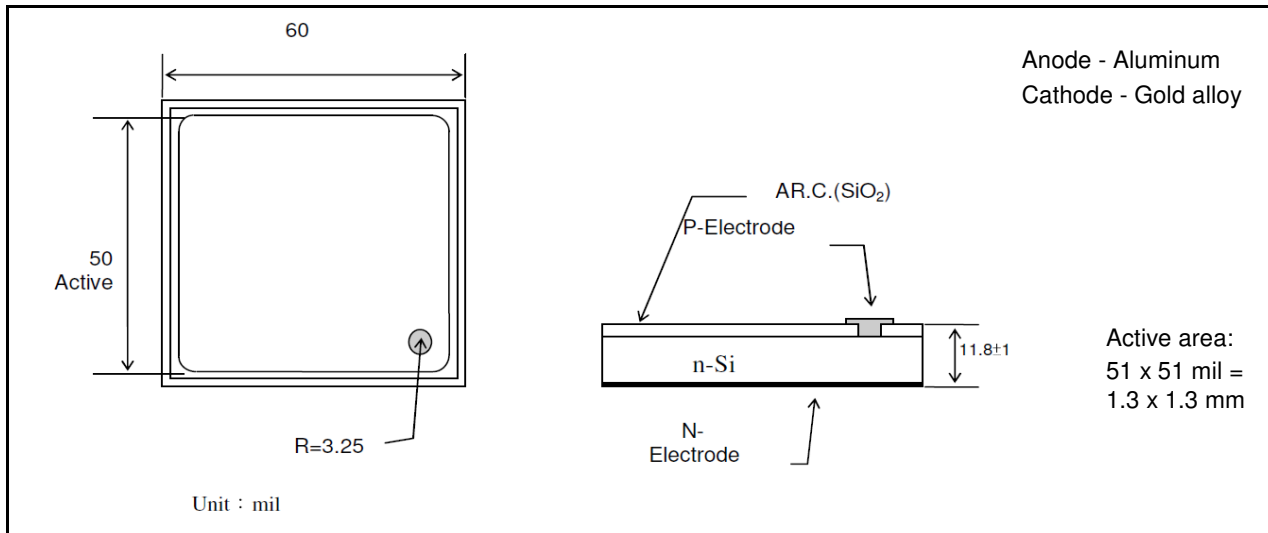


Photodiode Chip IR

EOPC-940-1.5

Rev. 03, 2017

Radiation	Type	Electrodes
infrared	Si, PIN, planar	p (anode) up



Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameters	Test conditions	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	0.5	0.9	1.3	V
Breakdown voltage	$I_R = 100 \text{ }\mu\text{A}$	60	150		V
Dark current	$V_R = 10 \text{ V}$			8	nA
Photocurrent	$V_R = 5 \text{ V}$	5	10.5	15	μA
Wavelength of peak sens.	λ_p		940		nm
Junction capacitance	$V_R = 3 \text{ V}, f = 1 \text{ MHz}$	1	4.5	8	pF

Art. No. 123 011



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.